



INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)	ATTY DOCKET NO. ITL1027US (P16711)	SERIAL NO. 10/696,204
	APPLICANT(S): YING ZHOU, ET AL.	
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U.S. PATENT DOCUMENTS

*EXAMINE R INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.						
	B.						
	C.						
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	E.						
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	H.						
	I.						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	J.							
	K.							
	L.							
	M.							
	N.							
	O.							

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>me</i>	P.	Robert M. Wallace, "Challenges for the Characterization and Integration of High-k Gate Dielectrics," pp. 1-50, Nov. 2002, http://www.mtsc.unt.edu/lemd/Presentations/AVS%202002%20Invited%20Talk.pdf
<i>me</i>	Q.	Gerry Lucovsky, "The Physics and Chemistry of High-k Dielectrics and their Interfaces," pp. 1-49, available on June 2003, at http://www.semtech.org/public/news/conferences/Reliability4/Documents/03_Gate_Stack_Transistor_Lucovsky.pdf
	R.	
	S.	
	T.	

EXAMINER *Michelle Estrada*DATE CONSIDERED *9/27/04*

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.